



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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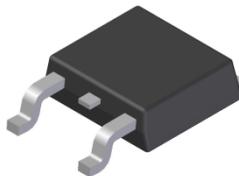
## Features

- $BV_{CEO} > -50V$
- $I_C = -3A$  High Continuous Collector Current
- $I_{CM} = -4.5A$  Peak Pulse Current
- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Medium Power Switching or Amplification Applications

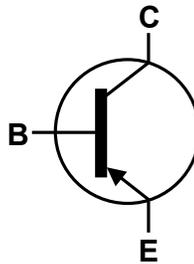
## Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.34 grams (approximate)

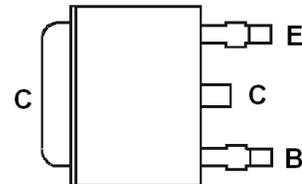
TO252 (DPAK)



Top View



Device Schematic



Pin Out Configuration  
Top view

### Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Continuous Collector Current	$I_C$	-3	A
Peak Pulse Collector Current	$I_{CM}$	-4.5	A

### Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

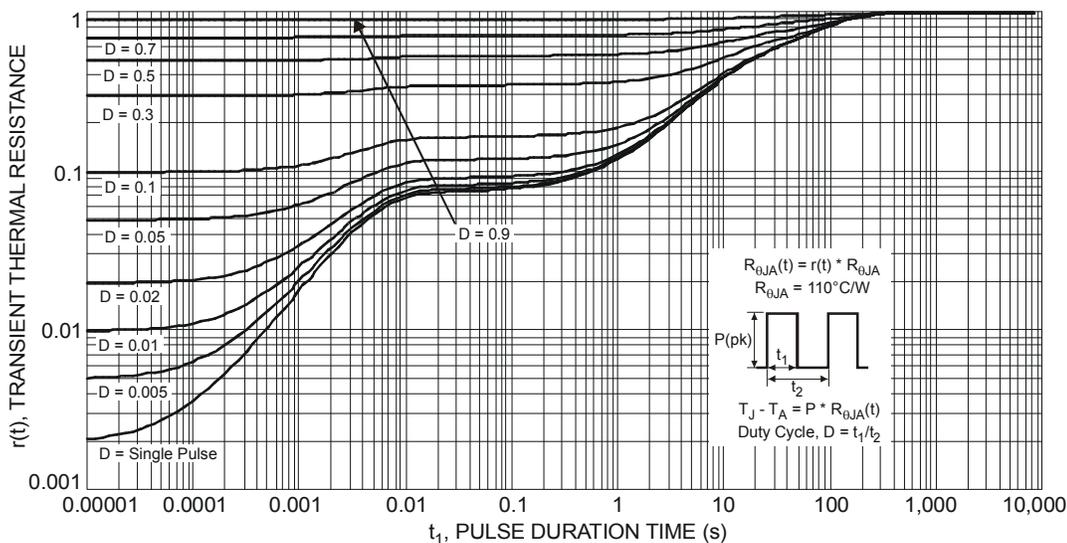
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_D$	1.2	W
Power Dissipation @ $T_L = +25^\circ\text{C}$ (Note 6)	$P_D$	15	W
Thermal Resistance, Junction to Lead (Note 5)	$R_{\theta JA}$	104	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JL}$	8.3	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Note:
- For a device mounted with the exposed collector pad on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  - Thermal resistance from junction to solder-point (on the exposed collector pad).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

### Thermal Characteristics



**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Collector-Base Breakdown Voltage	$BV_{CBO}$	-60	—	—	V	$I_C = -50\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	-50	—	—	V	$I_C = -1\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-5	—	—	V	$I_E = -50\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CBO}$	—	—	-1	$\mu\text{A}$	$V_{CB} = -40\text{V}, I_E = 0$
Emitter Cutoff Current	$I_{EBO}$	—	—	-1	$\mu\text{A}$	$V_{EB} = -4\text{V}, I_C = 0$
<b>ON CHARACTERISTICS (Note 8)</b>						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	-1	V	$I_C = -2\text{A}, I_B = -0.2\text{A}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	—	-1.2	V	$I_C = -1.5\text{A}, I_B = -0.15\text{A}$
DC Current Gain	$h_{FE}$	120	—	270	—	$V_{CE} = -3\text{V}, I_C = -0.5\text{A}$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Current Gain-Bandwidth Product	$f_T$	—	110	—	MHZ	$V_{CE} = -5\text{V}, I_C = -0.1\text{A}, f = 30\text{MHZ}$
Output Capacitance	$C_{obo}$	—	26	—	pF	$V_{CB} = -10\text{V}, f = 1\text{MHZ}$
Turn-On Time	$t_{on}$	—	109	—	ns	$V_{CC} = 30\text{V}$ $I_{CC} = 150\text{mA}$ $I_{B1} = -I_{B2} = 15\text{mA}$
Delay Time	$t_d$	—	60	—	ns	
Rise Time	$t_r$	—	49	—	ns	
Turn-Off Time	$t_{off}$	—	280	—	ns	
Storage Time	$t_s$	—	246	—	ns	
Fall Time	$t_f$	—	34	—	ns	

Note: 8. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

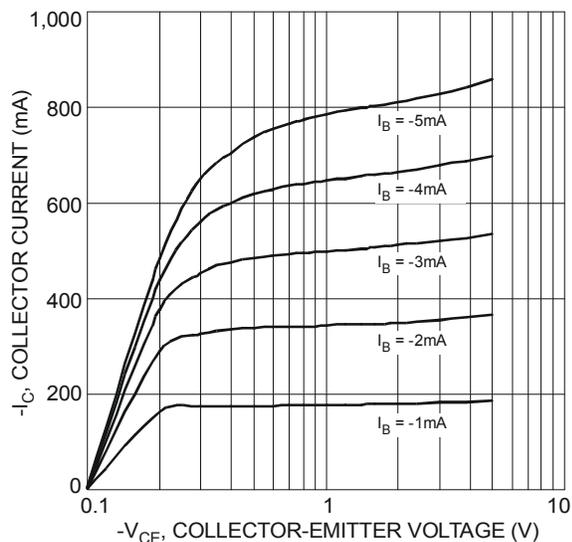


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

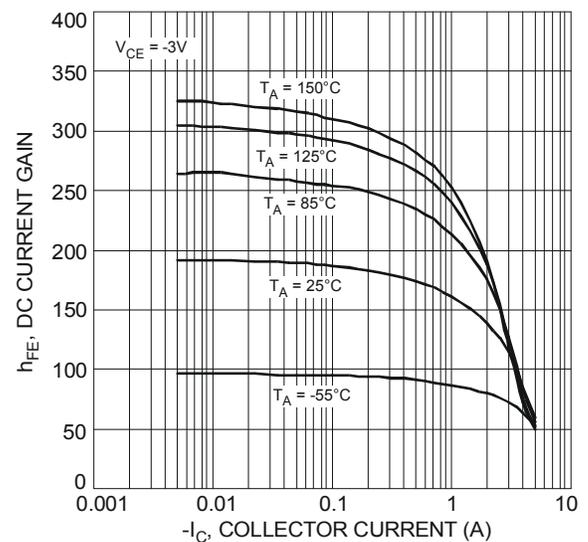


Figure 3 Typical DC Current Gain vs. Collector Current

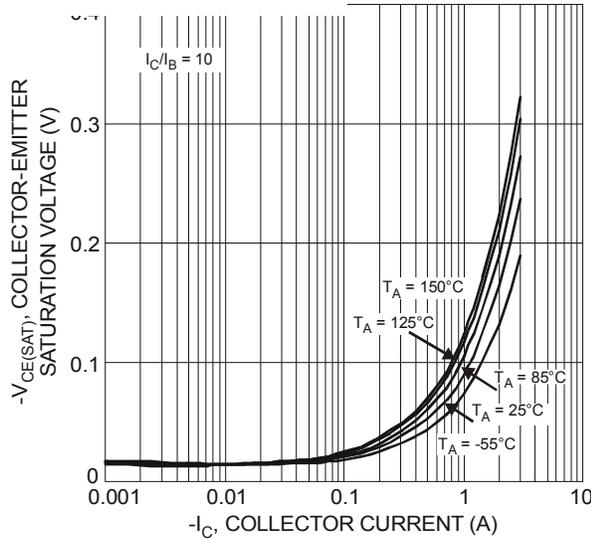


Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

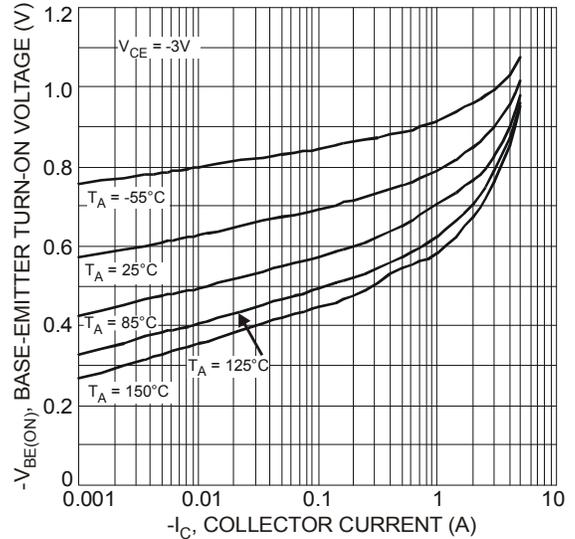


Figure 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

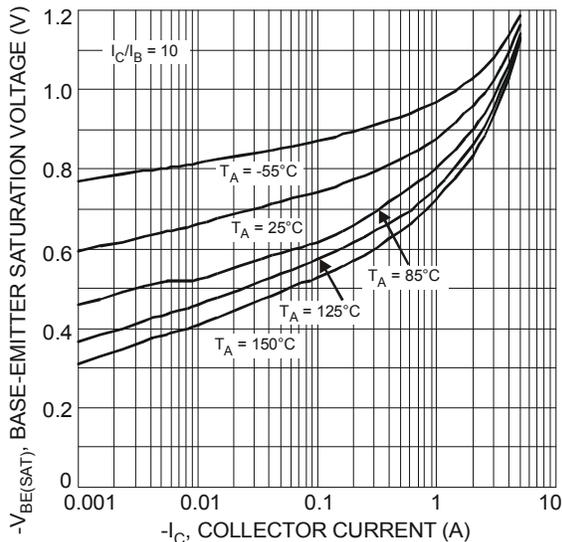


Figure 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

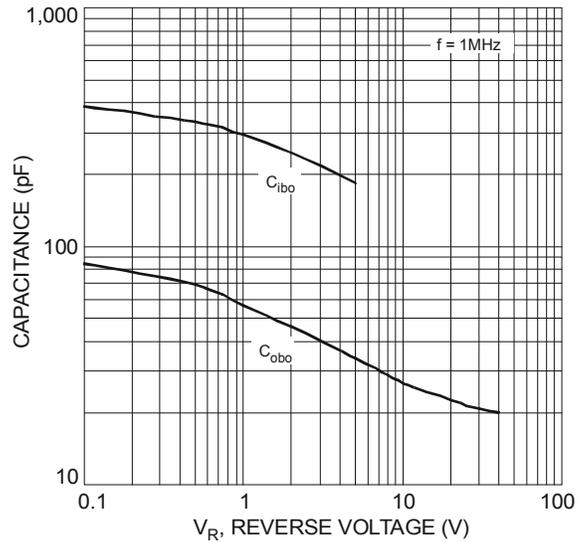


Figure 7 Typical Capacitance Characteristics

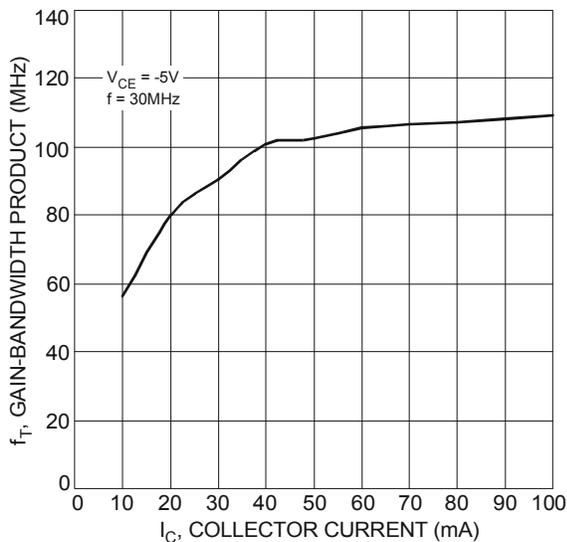


Figure 8 Typical Gain-Bandwidth Product vs. Collector Current

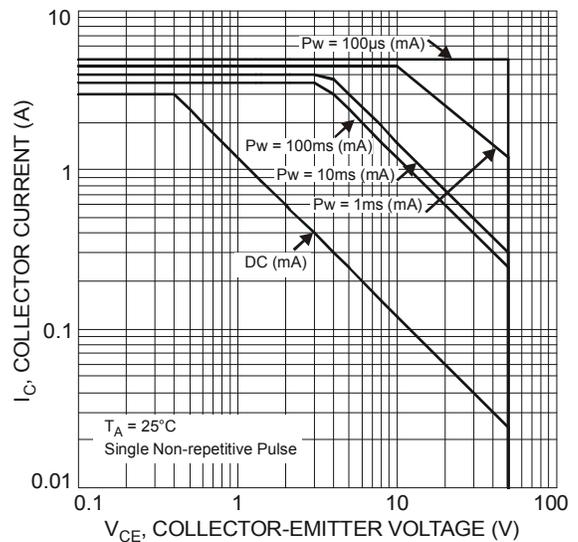
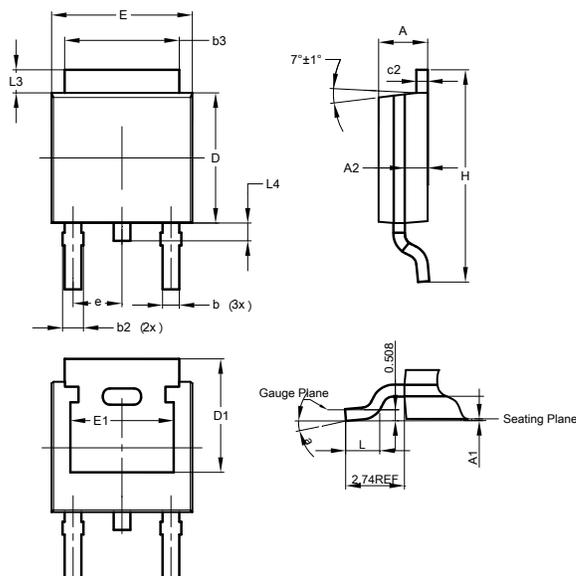


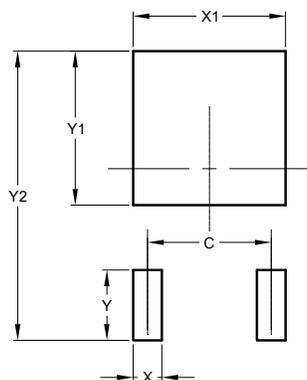
Figure 9 Safe Operating Area (Note 3)

### Package Outline Dimensions



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

### Suggested Pad Layout



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700